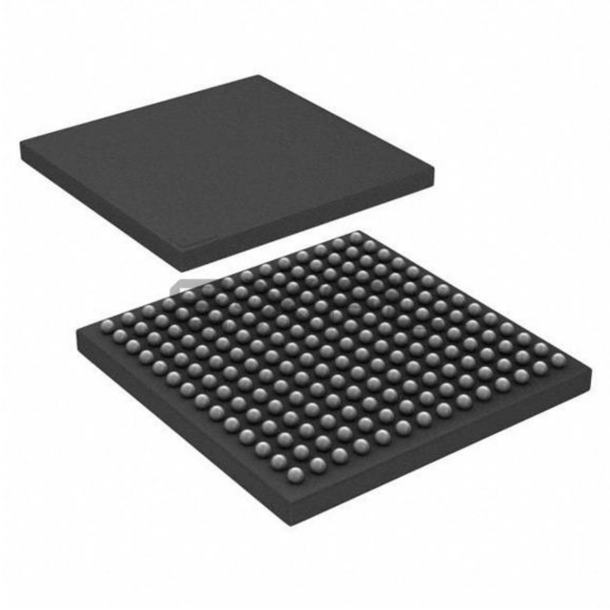
AMD Xilinx - XC7S15-1FTGB196I Datasheet



Welcome to E-XFL.COM

Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	1000
Number of Logic Elements/Cells	12800
Total RAM Bits	368640
Number of I/O	100
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	196-LBGA, CSPBGA
Supplier Device Package	196-CSBGA (15x15)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7s15-1ftgb196i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Table 4: **V_{IN} Maximum Allowed AC Voltage Overshoot and Undershoot for HR I/O Banks(1)(2)**

AC Voltage Overshoot	% of UI at –40°C to 125°C	AC Voltage Undershoot	% of UI at –40°C to 125°C
V_{CCO} + 0.55	100	–0.40	100
		–0.45	61.7
		–0.50	25.8
		–0.55	11.0
V_{CCO} + 0.60	46.6	–0.60	4.77
V_{CCO} + 0.65	21.2	–0.65	2.10
V_{CCO} + 0.70	9.75	–0.70	0.94
V_{CCO} + 0.75	4.55	–0.75	0.43
V_{CCO} + 0.80	2.15	–0.80	0.20
V_{CCO} + 0.85	1.02	–0.85	0.09
V_{CCO} + 0.90	0.49	–0.90	0.04
V_{CCO} + 0.95	0.24	–0.95	0.02

Notes:

1. A total of 200 mA per bank should not be exceeded.
2. The peak voltage of the overshoot or undershoot, and the duration above V_{CCO} + 0.20V or below GND – 0.20V, must not exceed the values in this table.

Table 5: **Typical Quiescent Supply Current(1)(2)(3)**

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
I_{CCINTQ}	Quiescent V_{CCINT} supply current.	XC7S6	36	36	36	36	36	32	mA
		XC7S15	36	36	36	36	36	32	mA
		XC7S25	48	48	48	48	48	43	mA
		XC7S50	95	95	95	95	95	59	mA
		XC7S75	148	148	148	148	148	134	mA
		XC7S100	148	148	148	148	148	134	mA
		XA7S6	N/A	36	N/A	36	36	N/A	mA
		XA7S15	N/A	36	N/A	36	36	N/A	mA
		XA7S25	N/A	48	N/A	48	48	N/A	mA
		XA7S50	N/A	95	N/A	95	95	N/A	mA
		XA7S75	N/A	148	N/A	148	148	N/A	mA
		XA7S100	N/A	148	N/A	148	148	N/A	mA

Table 5: **Typical Quiescent Supply Current[(1)(2)(3)]** ***(Cont'd)***

Symbol	Description	Device	Speed Grade						Units
			1.0V					0.95V	
			-2C	-2I	-1C	-1I	-1Q	-1LI	
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XC7S6	1	1	1	1	1	1	mA
		XC7S15	1	1	1	1	1	1	mA
		XC7S25	1	1	1	1	1	1	mA
		XC7S50	2	2	2	2	2	1	mA
		XC7S75	9	9	9	9	9	8	mA
		XC7S100	9	9	9	9	9	8	mA
		XA7S6	N/A	1	N/A	1	1	N/A	mA
		XA7S15	N/A	1	N/A	1	1	N/A	mA
		XA7S25	N/A	1	N/A	1	1	N/A	mA
		XA7S50	N/A	2	N/A	2	2	N/A	mA
		XA7S75	N/A	9	N/A	9	9	N/A	mA
		XA7S100	N/A	9	N/A	9	9	N/A	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperature (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the *Xilinx Power Estimator* spreadsheet tool [Ref 6] to estimate static power consumption for conditions other than those specified.

Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0 the following conditions apply.

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

There is no recommended sequence for supplies not discussed in this section.

DC Input and Output Levels

Values for V_{IL} and V_{IH} are recommended input voltages. Values for I_{OL} and I_{OH} are guaranteed over the recommended operating conditions at the V_{OL} and V_{OH} test points. Only selected standards are tested. These are chosen to ensure that all standards meet their specifications. The selected standards are tested at a minimum V_{CCO} with the respective V_{OL} and V_{OH} voltage levels shown. Other standards are sample tested.

Table 8: **SelectIO DC Input and Output Levels**(1)(2)(3)

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 6	Note 6
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 6	Note 6
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471) [Ref 3].
4. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
6. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.

Table 15: **Networking Applications Interface Performances *(Cont'd)***

Description	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
DDR LVDS receiver(1)	1250	950	950	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications where specific dynamic phase-alignment (DPA) algorithms dominate deterministic performance.

Table 16: **Maximum Physical Interface (PHY) Rate for Memory Interface IP available with the Memory Interface Generator(1)**

Memory Standard	V_{CCINT} Operating Voltage, Speed Grade, and Temperature Range			Units
	1.0V		0.95V	
	-2C/-2I	-1C/-1I/-1Q	-1LI	
4:1 Memory Controllers				
DDR3	800(2)	667	667	Mb/s
DDR3L	800(2)	667	667	Mb/s
DDR2	800(2)	667	667	Mb/s
2:1 Memory Controllers				
DDR3	800(2)	667	667	Mb/s
DDR3L	800(2)	667	667	Mb/s
DDR2	800(2)	667	667	Mb/s
LPDDR2	667	533	533	Mb/s

Notes:

1. V_{REF} tracking is required. For more information, see the *Zynq-7000 AP SoC and 7 Series FPGAs Memory Interface Solutions User Guide* (UG586) [Ref 7].
2. The maximum PHY rate is 667 Mb/s in the FTGB196 package.

IOB Pad Input/Output/3-State

Table 17 summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- T_{IOPI} is described as the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- T_{IOOP} is described as the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- T_{IOTP} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HR I/O banks, the IN_TERM termination turn-on time is always faster than T_{IOTP} when the INTERMDISABLE pin is used.

Table 17: **IOB High Range (HR) Switching Characteristics**

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVTTL_S4	1.34	1.41	1.41	3.93	4.18	4.18	3.96	4.20	4.20	ns
LVTTL_S8	1.34	1.41	1.41	3.66	3.92	3.92	3.69	3.93	3.93	ns
LVTTL_S12	1.34	1.41	1.41	3.65	3.90	3.90	3.68	3.91	3.91	ns
LVTTL_S16	1.34	1.41	1.41	3.19	3.45	3.45	3.22	3.46	3.46	ns
LVTTL_S24	1.34	1.41	1.41	3.41	3.67	3.67	3.44	3.68	3.68	ns
LVTTL_F4	1.34	1.41	1.41	3.38	3.64	3.64	3.41	3.65	3.65	ns
LVTTL_F8	1.34	1.41	1.41	2.87	3.12	3.12	2.90	3.13	3.13	ns
LVTTL_F12	1.34	1.41	1.41	2.85	3.10	3.10	2.88	3.12	3.12	ns
LVTTL_F16	1.34	1.41	1.41	2.68	2.93	2.93	2.71	2.95	2.95	ns
LVTTL_F24	1.34	1.41	1.41	2.65	2.90	2.90	2.68	2.91	2.91	ns
LVDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns
MINI_LVDS_25	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns
BLVDS_25	0.81	0.88	0.88	1.96	2.21	2.21	1.99	2.23	2.23	ns
RSDS_25 (point to point)	0.81	0.88	0.88	1.40	1.65	1.65	1.43	1.66	1.66	ns
PPDS_25	0.81	0.88	0.88	1.41	1.67	1.67	1.44	1.68	1.68	ns
TMDS_33	0.81	0.88	0.88	1.54	1.79	1.79	1.57	1.80	1.80	ns
PCI33_3	1.32	1.39	1.39	3.22	3.48	3.48	3.25	3.49	3.49	ns
HSUL_12_S	0.75	0.82	0.82	1.93	2.18	2.18	1.96	2.20	2.20	ns
HSUL_12_F	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns
DIFF_HSUL_12_S	0.76	0.83	0.83	1.93	2.18	2.18	1.96	2.20	2.20	ns
DIFF_HSUL_12_F	0.76	0.83	0.83	1.41	1.67	1.67	1.44	1.68	1.68	ns
MOBILE_DDR_S	0.84	0.91	0.91	1.80	2.06	2.06	1.83	2.07	2.07	ns
MOBILE_DDR_F	0.84	0.91	0.91	1.51	1.76	1.76	1.54	1.77	1.77	ns
DIFF_MOBILE_DDR_S	0.78	0.85	0.85	1.82	2.07	2.07	1.85	2.09	2.09	ns
DIFF_MOBILE_DDR_F	0.78	0.85	0.85	1.57	1.82	1.82	1.60	1.84	1.84	ns
HSTL_I_S	0.75	0.82	0.82	1.74	1.99	1.99	1.77	2.01	2.01	ns
HSTL_II_S	0.73	0.80	0.80	1.54	1.79	1.79	1.57	1.80	1.80	ns
HSTL_I_18_S	0.75	0.82	0.82	1.41	1.67	1.67	1.44	1.68	1.68	ns
HSTL_II_18_S	0.75	0.81	0.81	1.54	1.79	1.79	1.57	1.80	1.80	ns
DIFF_HSTL_I_S	0.76	0.83	0.83	1.71	1.96	1.96	1.74	1.98	1.98	ns
DIFF_HSTL_II_S	0.76	0.83	0.83	1.63	1.88	1.88	1.66	1.90	1.90	ns
DIFF_HSTL_I_18_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
DIFF_HSTL_II_18_S	0.78	0.85	0.85	1.58	1.84	1.84	1.61	1.85	1.85	ns
HSTL_I_F	0.75	0.82	0.82	1.22	1.48	1.48	1.25	1.49	1.49	ns
HSTL_II_F	0.73	0.80	0.80	1.24	1.49	1.49	1.27	1.51	1.51	ns
HSTL_I_18_F	0.75	0.82	0.82	1.26	1.51	1.51	1.29	1.52	1.52	ns

Table 17: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	V_{CCINT} Operating Voltage and Speed Grade									
	1.0V		0.95V	1.0V		0.95V	1.0V		0.95V	
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVCMOS15_F8	0.86	0.93	0.93	1.72	1.98	1.98	1.75	1.99	1.99	ns
LVCMOS15_F12	0.86	0.93	0.93	1.47	1.73	1.73	1.50	1.74	1.74	ns
LVCMOS15_F16	0.86	0.93	0.93	1.46	1.71	1.71	1.49	1.73	1.73	ns
LVCMOS12_S4	0.95	1.02	1.02	2.69	2.95	2.95	2.72	2.96	2.96	ns
LVCMOS12_S8	0.95	1.02	1.02	2.21	2.46	2.46	2.24	2.48	2.48	ns
LVCMOS12_S12	0.95	1.02	1.02	1.91	2.17	2.17	1.94	2.18	2.18	ns
LVCMOS12_F4	0.95	1.02	1.02	2.10	2.35	2.35	2.13	2.37	2.37	ns
LVCMOS12_F8	0.95	1.02	1.02	1.66	1.92	1.92	1.69	1.93	1.93	ns
LVCMOS12_F12	0.95	1.02	1.02	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_S	0.75	0.82	0.82	1.47	1.73	1.73	1.50	1.74	1.74	ns
SSTL15_S	0.68	0.75	0.75	1.43	1.68	1.68	1.46	1.69	1.69	ns
SSTL18_I_S	0.75	0.82	0.82	1.79	2.04	2.04	1.82	2.06	2.06	ns
SSTL18_II_S	0.75	0.82	0.82	1.43	1.68	1.68	1.46	1.70	1.70	ns
DIFF_SSTL135_S	0.76	0.83	0.83	1.47	1.73	1.73	1.50	1.74	1.74	ns
DIFF_SSTL15_S	0.76	0.83	0.83	1.43	1.68	1.68	1.46	1.69	1.69	ns
DIFF_SSTL18_I_S	0.79	0.86	0.86	1.80	2.06	2.06	1.83	2.07	2.07	ns
DIFF_SSTL18_II_S	0.79	0.86	0.86	1.51	1.76	1.76	1.54	1.77	1.77	ns
SSTL135_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL15_F	0.68	0.75	0.75	1.19	1.45	1.45	1.22	1.46	1.46	ns
SSTL18_I_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
SSTL18_II_F	0.75	0.82	0.82	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL135_F	0.76	0.83	0.83	1.24	1.49	1.49	1.27	1.51	1.51	ns
DIFF_SSTL15_F	0.76	0.83	0.83	1.19	1.45	1.45	1.22	1.46	1.46	ns
DIFF_SSTL18_I_F	0.79	0.86	0.86	1.35	1.60	1.60	1.38	1.62	1.62	ns
DIFF_SSTL18_II_F	0.79	0.86	0.86	1.33	1.59	1.59	1.36	1.60	1.60	ns

Table 18 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 1 and Figure 2.

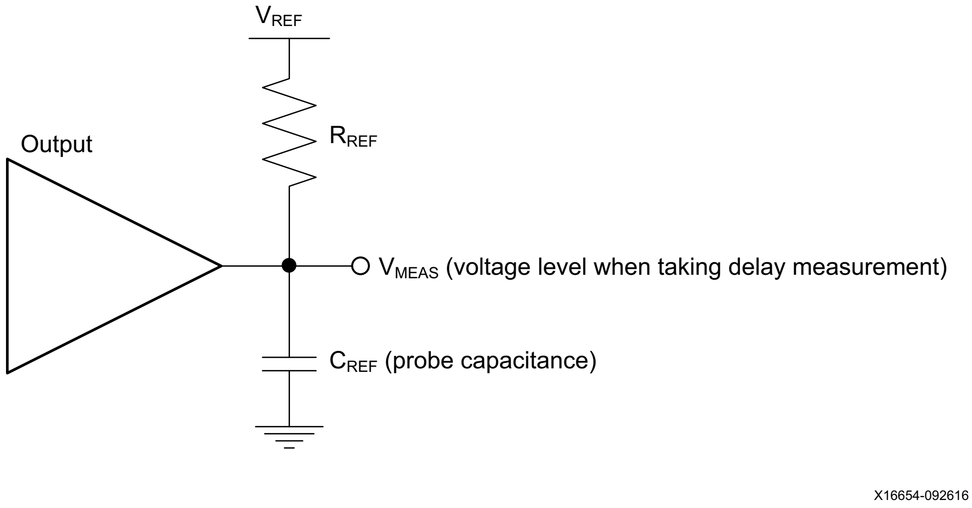


Figure 1: **Single-ended Test Setup**

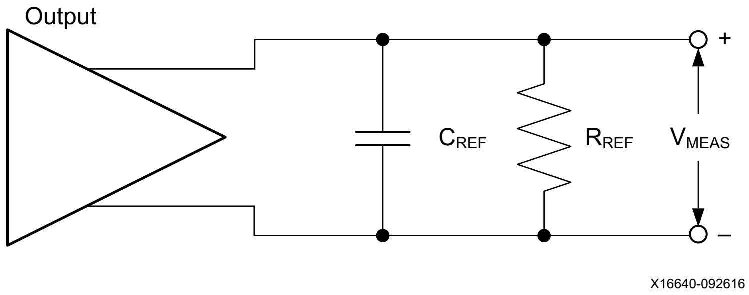


Figure 2: **Differential Test Setup**

Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using this method:

1. Simulate the output driver of choice into the generalized test setup using values from Table 20.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of step 2 and step 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Input/Output Logic Switching Characteristics

Table 21: **ILOGIC Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup/Hold					
T_{ICE1CK}/T_{ICKCE1}	CE1 pin setup/hold with respect to CLK.	0.54/0.02	0.76/0.02	0.76/0.02	ns
T_{ISRCK}/T_{ICKSR}	SR pin setup/hold with respect to CLK.	0.70/0.01	1.13/0.01	1.13/0.01	ns
T_{IDOCK}/T_{IOCKD}	D pin setup/hold with respect to CLK without delay.	0.01/0.29	0.01/0.33	0.01/0.33	ns
T_{IDOCKD}/T_{IOCKDD}	DDLY pin setup/hold with respect to CLK (using IDELAY).	0.02/0.29	0.02/0.33	0.02/0.33	ns
Combinatorial					
T_{IDI}	D pin to O pin propagation delay, no delay.	0.11	0.13	0.13	ns
T_{IDID}	DDLY pin to O pin propagation delay (using IDELAY).	0.12	0.14	0.14	ns
Sequential Delays					
T_{IDLO}	D pin to Q1 pin using flip-flop as a latch without delay.	0.44	0.51	0.51	ns
T_{IDLOD}	DDLY pin to Q1 pin using flip-flop as a latch (using IDELAY).	0.44	0.51	0.51	ns
T_{ICKQ}	CLK to Q outputs.	0.57	0.66	0.66	ns
T_{RQ_ILOGIC}	SR pin to OQ/TQ out.	1.08	1.32	1.32	ns
T_{GSRQ_ILOGIC}	Global set/reset to Q outputs.	7.60	10.51	10.51	ns
Set/Reset					
T_{RPW_ILOGIC}	Minimum pulse width, SR inputs.	0.72	0.72	0.72	ns, Min

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 28: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Sequential Delays					
T_{SHCKO}	Clock to A – B outputs.	1.09	1.32	1.32	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs.	1.53	1.86	1.86	ns, Max
Setup and Hold Times Before/After Clock CLK					
T_{DS_LRAM}/T_{DH_LRAM}	A – D inputs to CLK.	0.60/0.30	0.72/0.35	0.72/0.35	ns, Min
T_{AS_LRAM}/T_{AH_LRAM}	Address An inputs to clock.	0.30/0.60	0.37/0.70	0.37/0.70	ns, Min
	Address An inputs through MUXs and/or carry logic to clock.	0.77/0.21	0.94/0.26	0.94/0.26	ns, Min
T_{WS_LRAM}/T_{WH_LRAM}	WE input to clock.	0.43/0.12	0.53/0.17	0.53/0.17	ns, Min
$T_{CECK\_LRAM}/T_{CKCE\_LRAM}$	CE input to CLK.	0.44/0.11	0.53/0.17	0.53/0.17	ns, Min
Clock CLK					
T_{MPW_LRAM}	Minimum pulse width.	1.13	1.25	1.25	ns, Min
T_{MCP}	Minimum clock period.	2.26	2.50	2.50	ns, Min

Notes:

1. T_{SHCKO} also represents the CLK to XMUX output. Refer to the timing report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 29: **CLB Shift Register Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Sequential Delays					
T_{REG}	Clock to A – D outputs.	1.33	1.61	1.61	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output.	1.77	2.15	2.15	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output.	1.23	1.46	1.46	ns, Max
Setup and Hold Times Before/After Clock CLK					
$T_{WS\_SHFREG}/ T_{WH\_SHFREG}$	WE input.	0.41/0.12	0.51/0.17	0.51/0.17	ns, Min
$T_{CECK\_SHFREG}/ T_{CKCE\_SHFREG}$	CE input to CLK.	0.42/0.11	0.52/0.17	0.52/0.17	ns, Min
$T_{DS\_SHFREG}/ T_{DH\_SHFREG}$	A – D inputs to CLK.	0.37/0.37	0.44/0.43	0.44/0.43	ns, Min
Clock CLK					
T_{MPW_SHFREG}	Minimum pulse width.	0.86	0.98	0.98	ns, Min

Block RAM and FIFO Switching Characteristics

Table 30: **Block RAM and FIFO Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Block RAM and FIFO Clock-to-Out Delays					
T_{RCKO_DO} and $T_{RCKO\_DO\_REG}$	Clock CLK to DOUT output (without output register).(1)(2)	2.13	2.46	2.46	ns, Max
	Clock CLK to DOUT output (with output register).(3)(4)	0.74	0.89	0.89	ns, Max
$T_{RCKO\_DO\_ECC}$ and $T_{RCKO\_DO\_ECC\_REG}$	Clock CLK to DOUT output with ECC (without output register).(1)(2)	3.04	3.84	3.84	ns, Max
	Clock CLK to DOUT output with ECC (with output register).(3)(4)	0.81	0.94	0.94	ns, Max
$T_{RCKO\_DO\_CASCOUT}$ and $T_{RCKO\_DO\_CASCOUT\_REG}$	Clock CLK to DOUT output with cascade (without output register).(1)	2.88	3.30	3.30	ns, Max
	Clock CLK to DOUT output with cascade (with output register).(3)	1.28	1.46	1.46	ns, Max
T_{RCKO_FLAGS}	Clock CLK to FIFO flags outputs.(5)	0.87	1.05	1.05	ns, Max
$T_{RCKO\_POINTERS}$	Clock CLK to FIFO pointers outputs.(6)	1.02	1.15	1.15	ns, Max
$T_{RCKO\_PARITY\_ECC}$	Clock CLK to ECCPARITY in ECC encode only mode.	0.85	0.94	0.94	ns, Max
$T_{RCKO\_SDBIT\_ECC}$ and $T_{RCKO\_SDBIT\_ECC\_REG}$	Clock CLK to BITERR (without output register).	2.81	3.55	3.55	ns, Max
	Clock CLK to BITERR (with output register).	0.76	0.89	0.89	ns, Max
$T_{RCKO\_RDADDR\_ECC}$ and $T_{RCKO\_RDADDR\_ECC\_REG}$	Clock CLK to RDADDR output with ECC (without output register).	0.88	1.07	1.07	ns, Max
	Clock CLK to RDADDR output with ECC (with output register).	0.93	1.08	1.08	ns, Max
Setup and Hold Times Before/After Clock CLK					
T_{RCCK_ADDRA}/ T_{RCKC_ADDRA}	ADDR inputs.(7)	0.49/0.33	0.57/0.36	0.57/0.36	ns, Min
$T_{RDCK\_DI\_WF\_NC}$/ $T_{RCKD\_DI\_WF\_NC}$	Data input setup/hold time when block RAM is configured in WRITE_FIRST or NO_CHANGE mode.(8)	0.65/0.63	0.74/0.67	0.74/0.67	ns, Min
$T_{RDCK\_DI\_RF}$/ $T_{RCKD\_DI\_RF}$	Data input setup/hold time when block RAM is configured in READ_FIRST mode.(8)	0.22/0.34	0.25/0.41	0.25/0.41	ns, Min
$T_{RDCK\_DI\_ECC}$/ $T_{RCKD\_DI\_ECC}$	DIN inputs with block RAM ECC in standard mode.(8)	0.55/0.46	0.63/0.50	0.63/0.50	ns, Min
$T_{RDCK\_DI\_ECCW}$/ $T_{RCKD\_DI\_ECCW}$	DIN inputs with block RAM ECC encode only.(8)	1.02/0.46	1.17/0.50	1.17/0.50	ns, Min

DSP48E1 Switching Characteristics

Table 31: **DSP48E1 Switching Characteristics**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Setup and Hold Times of Data/Control Pins to the Input Register Clock					
$T_{DSPDCK\_A\_AREG}$/ $T_{DSPCKD\_A\_AREG}$	A input to A register CLK.	0.30/0.13	0.37/0.14	0.37/0.14	ns
$T_{DSPDCK\_B\_BREG}$/ $T_{DSPCKD\_B\_BREG}$	B input to B register CLK.	0.38/0.16	0.45/0.18	0.45/0.18	ns
$T_{DSPDCK\_C\_CREG}$/ $T_{DSPCKD\_C\_CREG}$	C input to C register CLK.	0.20/0.19	0.24/0.21	0.24/0.21	ns
$T_{DSPDCK\_D\_DREG}$/ $T_{DSPCKD\_D\_DREG}$	D input to D register CLK.	0.32/0.27	0.42/0.27	0.42/0.27	ns
$T_{DSPDCK\_ACIN\_AREG}$/ $T_{DSPCKD\_ACIN\_AREG}$	ACIN input to A register CLK.	0.27/0.13	0.32/0.14	0.32/0.14	ns
$T_{DSPDCK\_BCIN\_BREG}$/ $T_{DSPCKD\_BCIN\_BREG}$	BCIN input to B register CLK.	0.29/0.16	0.36/0.18	0.36/0.18	ns
Setup and Hold Times of Data Pins to the Pipeline Register Clock					
$T_{DSPDCK\_\{A, B\}\_MREG\_MULT}$/ $T_{DSPCKD\_\{A, B\}\_MREG\_MULT}$	{A, B} input to M register CLK using multiplier.	2.76/–0.01	3.29/–0.01	3.29/–0.01	ns
$T_{DSPDCK\_\{A, D\}\_ADREG}$/ $T_{DSPCKD\_\{A, D\}\_ADREG}$	{A, D} input to AD register CLK.	1.48/–0.02	1.76/–0.02	1.76/–0.02	ns
Setup and Hold Times of Data/Control Pins to the Output Register Clock					
$T_{DSPDCK\_\{A, B\}\_PREG\_MULT}$/ $T_{DSPCKD\_\{A, B\}\ \_PREG\_MULT}$	{A, B} input to P register CLK using multiplier.	4.60/–0.28	5.48/–0.28	5.48/–0.28	ns
$T_{DSPDCK\_D\_PREG\_MULT}$/ $T_{DSPCKD\_D\_PREG\_MULT}$	D input to P register CLK using multiplier.	4.50/–0.73	5.35/–0.73	5.35/–0.73	ns
$T_{DSPDCK\_\{A, B\}\ \_PREG}$/ $T_{DSPCKD\_\{A, B\}\ \_PREG}$	A or B input to P register CLK not using multiplier.	1.98/–0.28	2.35/–0.28	2.35/–0.28	ns
$T_{DSPDCK\_C\_PREG}$/ $T_{DSPCKD\_C\_PREG}$	C input to P register CLK not using multiplier.	1.76/–0.26	2.10/–0.26	2.10/–0.26	ns
$T_{DSPDCK\_PCIN\_PREG}$/ $T_{DSPCKD\_PCIN\_PREG}$	PCIN input to P register CLK.	1.51/–0.15	1.80/–0.15	1.80/–0.15	ns
Setup and Hold Times of the CE Pins					
$T_{DSPDCK\_\{CEA;CEB\}\_\{AREG;BREG\}}$/ $T_{DSPCKD\_\{CEA;CEB\}\_\{AREG;BREG\}}$	{CEA; CEB} input to {A; B} register CLK.	0.42/0.08	0.52/0.11	0.52/0.11	ns
$T_{DSPDCK\_CEC\_CREG}$/ $T_{DSPCKD\_CEC\_CREG}$	CEC input to C register CLK.	0.34/0.11	0.42/0.13	0.42/0.13	ns
$T_{DSPDCK\_CED\_DREG}$/ $T_{DSPCKD\_CED\_DREG}$	CED input to D register CLK.	0.43/–0.03	0.52/–0.03	0.52/–0.03	ns

Clock Buffers and Networks

Table 32: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BCCCK_CE}/T_{BCCKC_CE}(1)	CE pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T_{BCCCK_S}/ T_{BCCKC_S}(1)	S pins setup/hold.	0.13/0.40	0.16/0.41	0.16/0.41	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O.	0.09	0.10	0.10	ns
Maximum Frequency					
F_{MAX_BUFG}	Global clock tree (BUFG).	628.00	464.00	464.00	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 33: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BIOCKO_O}	Clock to out delay from I to O.	1.26	1.54	1.54	ns
Maximum Frequency					
F_{MAX_BUFIO}	I/O clock tree (BUFIO).	680.00	600.00	600.00	MHz

Table 34: **Regional Clock Buffer Switching Characteristics (BUFR)**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
T_{BRCKO_O}	Clock to out delay from I to O.	0.76	0.99	0.99	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set.	0.39	0.52	0.52	ns
T_{BRDO_O}	Propagation delay from CLR to O.	0.85	1.09	1.09	ns
Maximum Frequency					
F_{MAX_BUFR}(1)	Regional clock tree (BUFR).	375.00	315.00	315.00	MHz

Notes:

1. The maximum input frequency to the BUFR is the BUFIO F_{MAX} frequency.

MMCM Switching Characteristics

Table 37: **MMCM Specification**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
MMCM_F_{INMAX}	Maximum input clock frequency.	800.00	800.00	800.00	MHz
MMCM_F_{INMIN}	Minimum input clock frequency.	10.00	10.00	10.00	MHz
MMCM_$F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max			
MMCM_F_{INDUTY}	Allowable input duty cycle: 10—49 MHz.	25	25	25	%
	Allowable input duty cycle: 50—199 MHz.	30	30	30	%
	Allowable input duty cycle: 200—399 MHz.	35	35	35	%
	Allowable input duty cycle: 400—499 MHz.	40	40	40	%
	Allowable input duty cycle: > 500 MHz.	45	45	45	%
MMCM_F_{MIN_PSCLK}	Minimum dynamic phase-shift clock frequency.	0.01	0.01	0.01	MHz
MMCM_F_{MAX_PSCLK}	Maximum dynamic phase-shift clock frequency.	500.00	450.00	450.00	MHz
MMCM_F_{VCOMIN}	Minimum MMCM VCO frequency.	600.00	600.00	600.00	MHz
MMCM_F_{VCOMAX}	Maximum MMCM VCO frequency.	1440.00	1200.00	1200.00	MHz
MMCM_$F_{BANDWIDTH}$	Low MMCM bandwidth at typical.(1)	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.(1)	4.00	4.00	4.00	MHz
MMCM_$T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.(2)	0.12	0.12	0.12	ns
MMCM_$T_{OUTJITTER}$	MMCM output jitter.	Note 3			
MMCM_$T_{OUTDUTY}$	MMCM output clock duty-cycle precision.(4)	0.20	0.20	0.20	ns
MMCM_$T_{LOCKMAX}$	MMCM maximum lock time.	100.00	100.00	100.00	µs
MMCM_F_{OUTMAX}	MMCM maximum output frequency.	800.00	800.00	800.00	MHz
MMCM_F_{OUTMIN}	MMCM minimum output frequency.(5)(6)	4.69	4.69	4.69	MHz
MMCM_$T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max			
MMCM_$RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	ns
MMCM_F_{PFDMAX}	Maximum frequency at the phase frequency detector.	500.00	450.00	450.00	MHz
MMCM_F_{PFDMIN}	Minimum frequency at the phase frequency detector.	10.00	10.00	10.00	MHz
MMCM_$T_{FBDELAY}$	Maximum delay in the feedback path.	3 ns Max or one CLKIN cycle			
MMCM Switching Characteristics Setup and Hold					
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and hold of phase-shift enable.	1.04/0.00	1.04/0.00	1.04/0.00	ns

Device Pin-to-Pin Output Parameter Guidelines

Table 39: **Clock-Capable Clock Input to Output Delay Without MMCM/PLL (Near Clock Region)[(1)]**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM/PLL.						
T_{ICKOF}	Clock-capable clock input and OUTFF at pins/banks closest to the BUFGs *without* MMCM/PLL (near clock region).(2)	XC7S6	5.55	6.50	6.50	ns
		XC7S15	5.55	6.50	6.50	ns
		XC7S25	5.55	6.44	6.44	ns
		XC7S50	5.71	6.62	6.62	ns
		XC7S75	5.73	6.71	6.71	ns
		XC7S100	5.73	6.71	6.71	ns
		XA7S6	5.55	6.50	N/A	ns
		XA7S15	5.55	6.50	N/A	ns
		XA7S25	5.55	6.44	N/A	ns
		XA7S50	5.71	6.62	N/A	ns
		XA7S75	5.73	6.71	N/A	ns
		XA7S100	5.73	6.71	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. Refer to the *Die Level Bank Numbering Overview* section of the *7 Series FPGA Packaging and Pinout Specification* (UG475) [Ref 4].

Table 41: **Clock-Capable Clock Input to Output Delay With MMCM(1)**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* MMCM.						
$T_{ICKOFMMCMCC}$	Clock-capable clock input and OUTFF *with* MMCM.(2)	XC7S6	1.03	1.03	1.03	ns
		XC7S15	1.03	1.03	1.03	ns
		XC7S25	1.00	1.00	1.00	ns
		XC7S50	1.00	1.00	1.00	ns
		XC7S75	1.00	1.00	1.00	ns
		XC7S100	1.00	1.00	1.00	ns
		XA7S6	1.03	1.03	N/A	ns
		XA7S15	1.03	1.03	N/A	ns
		XA7S25	1.00	1.00	N/A	ns
		XA7S50	1.00	1.00	N/A	ns
		XA7S75	1.00	1.00	N/A	ns
		XA7S100	1.00	1.00	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 42: **Clock-Capable Clock Input to Output Delay With PLL**(1)

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *with* PLL.						
$T_{ICKOFPLLCC}$	Clock-capable clock input and OUTFF *with* PLL.(2)	XC7S6	0.85	0.85	0.85	ns
		XC7S15	0.85	0.85	0.85	ns
		XC7S25	0.83	0.83	0.83	ns
		XC7S50	0.83	0.83	0.83	ns
		XC7S75	0.83	0.83	0.83	ns
		XC7S100	0.83	0.83	0.83	ns
		XA7S6	0.85	0.85	N/A	ns
		XA7S15	0.85	0.85	N/A	ns
		XA7S25	0.83	0.83	N/A	ns
		XA7S50	0.83	0.83	N/A	ns
		XA7S75	0.83	0.83	N/A	ns
		XA7S100	0.83	0.83	N/A	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net.
2. PLL output jitter is already included in the timing calculation.

Table 43: **Pin-to-Pin, Clock-to-Out using BUFIO**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
SSTL15 Clock-Capable Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with BUFIO.					
$T_{ICKOFCS}$	Clock to out of I/O clock.	5.61	6.64	6.64	ns

Device Pin-to-Pin Input Parameter Guidelines

All devices are 100% functionally tested. Values are expressed in nanoseconds unless otherwise noted.

Table 44: **Global Clock Input Setup and Hold Without MMCM/PLL with ZHOLD_DELAY on HR I/O Banks**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for SSTL15 Standard.[1]						
T_{PSFD}/ T_{PHFD}	Full delay (legacy delay or default delay) global clock input and IFF[2] without MMCM/PLL with ZHOLD_DELAY on HR I/O banks.	XC7S6	2.76/–0.40	3.17/–0.40	3.17/–0.40	ns
		XC7S15	2.76/–0.40	3.17/–0.40	3.17/–0.40	ns
		XC7S25	2.67/–0.37	3.12/–0.37	3.12/–0.37	ns
		XC7S50	2.66/–0.28	3.11/–0.28	3.11/–0.28	ns
		XC7S75	2.91/–0.33	3.36/–0.33	3.36/–0.33	ns
		XC7S100	2.91/–0.33	3.36/–0.33	3.36/–0.33	ns
		XA7S6	2.76/–0.40	3.17/–0.40	N/A	ns
		XA7S15	2.76/–0.40	3.17/–0.40	N/A	ns
		XA7S25	2.67/–0.37	3.12/–0.37	N/A	ns
		XA7S50	2.66/–0.28	3.11/–0.28	N/A	ns
		XA7S75	2.91/–0.33	3.36/–0.33	N/A	ns
		XA7S100	2.91/–0.33	3.36/–0.33	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. IFF = Input flip-flop or latch.

Table 46: **Clock-Capable Clock Input Setup and Hold With PLL**

Symbol	Description	Device	V_{CCINT} Operating Voltage and Speed Grade			Units
			1.0V		0.95V	
			-2	-1	-1L	
Input Setup and Hold Time Relative to Clock-Capable Clock Input Signal for SSTL15 Standard.[1][2]						
$T_{PSPLLCC}$/ $T_{PHPLLCC}$	No delay clock-capable clock input and IFF[3] with PLL.	XC7S6	3.07/–0.17	3.69/–0.17	3.69/–0.17	ns
		XC7S15	3.07/–0.17	3.69/–0.17	3.69/–0.17	ns
		XC7S25	3.04/–0.19	3.64/–0.19	3.64/–0.19	ns
		XC7S50	3.15/–0.19	3.77/–0.19	3.77/–0.19	ns
		XC7S75	3.15/–0.19	3.78/–0.19	3.78/–0.19	ns
		XC7S100	3.15/–0.19	3.78/–0.19	3.78/–0.19	ns
		XA7S6	3.07/–0.17	3.69/–0.17	N/A	ns
		XA7S15	3.07/–0.17	3.69/–0.17	N/A	ns
		XA7S25	3.04/–0.19	3.64/–0.19	N/A	ns
		XA7S50	3.15/–0.19	3.77/–0.19	N/A	ns
		XA7S75	3.15/–0.19	3.78/–0.19	N/A	ns
		XA7S100	3.15/–0.19	3.78/–0.19	N/A	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. Use IBIS to determine any duty-cycle distortion incurred using various standards.
3. IFF = Input flip-flop or latch.

Table 47: **Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO**

Symbol	Description	V_{CCINT} Operating Voltage and Speed Grade			Units
		1.0V		0.95V	
		-2	-1	-1L	
Input Setup and Hold Time Relative to a Forwarded Clock Input Pin Using BUFIO for SSTL15 Standard.					
T_{PSCS}/T_{PHCS}	Setup and hold of I/O clock.	–0.38/1.46	–0.38/1.73	–0.38/1.76	ns

XADC Specifications

The *7 Series FPGAs Overview* (DS180) [Ref 1] and *XA Spartan-7 Automotive FPGA Data Sheet: Overview* (DS171) [Ref 2] list the devices that contain a 7 series XADC dual 12-Bit 1 MSPS analog-to-digital converter.

Table 50: **XADC Specifications**

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
V_{CCADC} = 1.8V ± 5%, V_{REFP} = 1.25V, V_{REFN} = 0V, ADCCLK = 26 MHz, –55°C ≤ T_j ≤ 125°C. Typical values at T_j = +40°C.						
ADC Accuracy(1)						
Resolution			12	–	–	Bits
Integral nonlinearity(2)	INL	–40°C ≤ T_j ≤ 100°C	–	–	±2	LSBs
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±3	LSBs
Differential nonlinearity	DNL	No missing codes, guaranteed monotonic.	–	–	±1	LSBs
Offset error	Unipolar	–40°C ≤ T_j ≤ 100°C	–	–	±8	LSBs
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±12	LSBs
	Bipolar	–55°C ≤ T_j ≤ 125°C	–	–	±4	LSBs
Gain error			–	–	±0.5	%
Offset matching			–	–	4	LSBs
Gain matching			–	–	0.3	%
Sample rate			–	–	1	MS/s
Signal to noise ratio(2)	SNR	F_{SAMPLE} = 500 KS/s, F_{IN} = 20 kHz	60	–	–	dB
RMS code noise		External 1.25V reference.	–	–	2	LSBs
		On-chip reference.	–	3	–	LSBs
Total harmonic distortion(2)	THD	F_{SAMPLE} = 500 KS/s, F_{IN} = 20 kHz	70	–	–	dB
Analog Inputs(3)						
ADC input ranges		Unipolar operation.	0	–	1	V
		Bipolar operation.	–0.5	–	+0.5	V
		Unipolar common mode range (FS input).	0	–	+0.5	V
		Bipolar common mode range (FS input).	+0.5	–	+0.6	V
Maximum external channel input ranges		Adjacent analog channels set within these ranges should not corrupt measurements on adjacent channels.	–0.1	–	V_{CCADC}	V
Full-resolution bandwidth	FRBW	Auxiliary channel full resolution bandwidth.	250	–	–	kHz
On-chip Sensors						
Temperature sensor error		–40°C ≤ T_j ≤ 100°C	–	–	±4	°C
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±6	°C
Supply sensor error		–40°C ≤ T_j ≤ 100°C	–	–	±1	%
		–55°C ≤ T_j < –40°C; 100°C < T_j ≤ 125°C	–	–	±2	%

Table 50: **XADC Specifications *(Cont'd)***

Parameter	Symbol	Comments/Conditions	Min	Typ	Max	Units
Conversion Rate[4]						
Conversion time: continuous	t_{CONV}	Number of ADCCLK cycles.	26	–	32	Cycles
Conversion time: event	t_{CONV}	Number of CLK cycles.	–	–	21	Cycles
DRP clock frequency	DCLK	DRP clock frequency.	8	–	250	MHz
ADC clock frequency	ADCCLK	Derived from DCLK.	1	–	26	MHz
DCLK duty cycle			40	–	60	%
XADC Reference[5]						
External reference	V_{REFP}	Externally supplied reference voltage.	1.20	1.25	1.30	V
On-chip reference		Ground V_{REFP} pin to AGND, $-40°C \leq T_j \leq 100°C$	1.2375	1.25	1.2625	V
		Ground VREFP pin to AGND, $-55°C \leq T_j < -40°C$; $100°C < T_j \leq 125°C$	1.225	1.25	1.275	V

Notes:

1. Offset and gain errors are removed by enabling the XADC automatic gain calibration feature. The values are specified for when this feature is enabled.
2. Only specified for bitstream option XADCEnhancedLinearity = ON.
3. For a detailed description, see the *ADC* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
4. For a detailed description, see the *Timing* chapter in the *7 Series FPGAs and Zynq-7000 AP SoC XADC Dual 12-Bit 1 MSPS Analog-to-Digital Converter User Guide* (UG480) [Ref 9].
5. Any variation in the reference voltage from the nominal V_{REFP} = 1.25V and V_{REFN} = 0V will result in a deviation from the ideal transfer function. This also impacts the accuracy of the internal sensor measurements (i.e., temperature and power supply). However, for external ratiometric type applications allowing reference to vary by ±4% is permitted.